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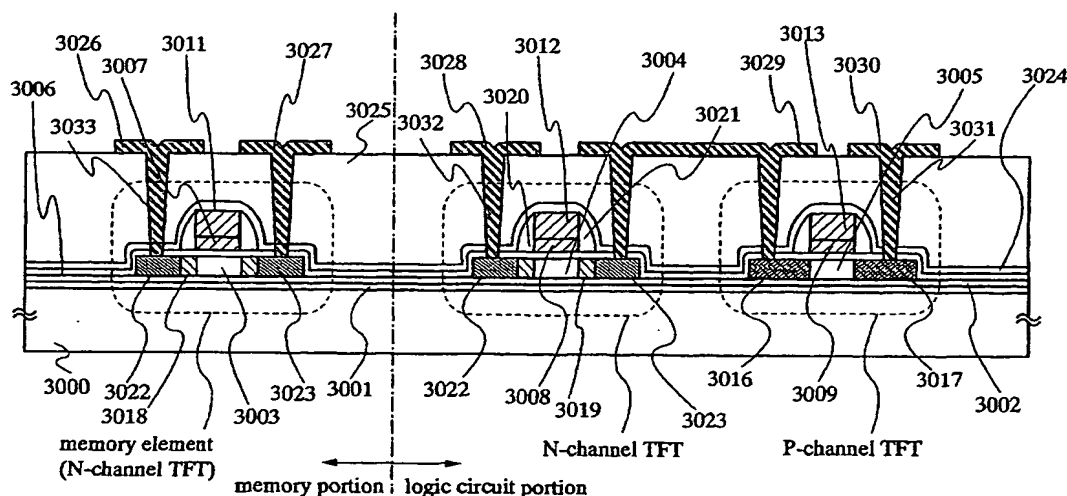
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(54) Title: MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE, AND IC CARD, IC TAG, RFID, TRANSPON-  
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(57) Abstract: The present invention provides a manufacturing method of a semiconductor device used as an ID chip, by which data can be written with improved throughput. According to the manufacturing method of a semiconductor device having a modulation circuit, a demodulation circuit, a logic circuit, a memory circuit, and an antenna circuit over an insulating substrate, the memory circuit is a nonvolatile memory circuit of which data is written in the manufacture of the semiconductor device, and elements in a data portion are formed by electron beam exposure or laser exposure while the other portions are formed by mirror projection exposure, step and repeat exposure, or step and scan exposure.